# P-Channel 60-V (D-S) MOSFET

### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

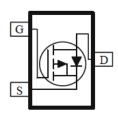
## **Typical Applications:**

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
-60	190 @ V <sub>GS</sub> = -10V	-1.1		
	230 @ V <sub>GS</sub> = -4.5V	-1.0		







ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)						
Parameter				Limit	Units	
Drain-Source Voltage				-60	V	
Gate-Source Voltage	je			±20	V	
Continuous Drain Current <sup>a</sup>		T <sub>A</sub> =25°C	ı	-1.1		
Continuous Drain Current		T <sub>A</sub> =70°C	l <sub>D</sub>	-0.9	Α	
Pulsed Drain Current <sup>b</sup>			$I_{DM}$	-5		
Continuous Source Current (Diode Conduction) a	I <sub>S</sub>	-0.5	Α			
Davier Dissipation 8		$T_A=25$ °C $T_A=70$ °C	P <sub>D</sub>	0.34	W	
Power Dissipation <sup>a</sup>			' D	0.22	v v	
Operating Junction and Storage Temperature Range				-55 to 150	°C	

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	100	°C/W			
Maximum Junction-to-Ambient	Steady State	IΛθJA	166	C/VV			

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### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

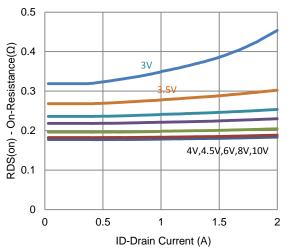
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zoro Coto Voltogo Drain Current		$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-1.5			Α	
Drain-Source On-Resistance <sup>a</sup>	r	$V_{GS} = -10 \text{ V}, I_{D} = -2 \text{ A}$			190	mΩ	
	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -1.6 \text{ A}$			230	11122	
Forward Transconductance a	g <sub>fs</sub>	$V_{DS} = -15 \text{ V}, I_{D} = -2 \text{ A}$		5		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -0.25 \text{ A}, V_{GS} = 0 \text{ V}$		-0.78		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	V = -30 V V = -4.5 V		4			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -30 \text{ V}, V_{GS} = -4.5 \text{ V},$ $I_{D} = -1 \text{ A}$		1.3		nC	
Gate-Drain Charge	$Q_gd$	1D = 174		1.6			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = -30 \text{ V}, R_{L} = 30 \Omega,$		7			
Rise Time	t <sub>r</sub>	$V_{DS} = -30 \text{ V}, \text{ K}_{L} = 30 \Omega,$ $I_{D} = -1 \text{ A},$		5		ne	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		11		ns	
Fall Time	t <sub>f</sub>	VGEN = 10 V, 11GEN = 0 12		7			
Input Capacitance	C <sub>iss</sub>			412			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		28		pF	
Reverse Transfer Capacitance	$C_{rss}$			22			

#### **Notes**

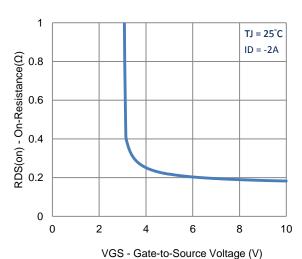
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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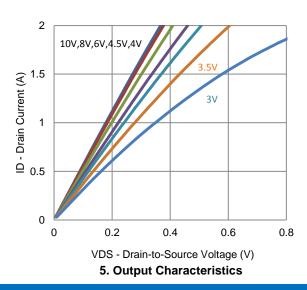
### **Typical Electrical Characteristics**



#### 1. On-Resistance vs. Drain Current

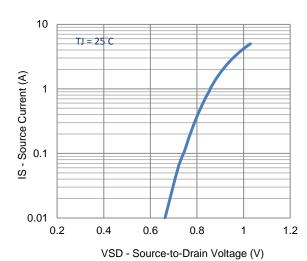


3. On-Resistance vs. Gate-to-Source Voltage

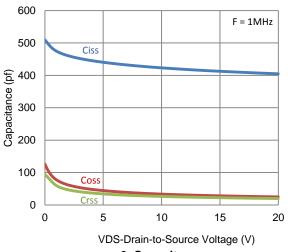


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(Y) 1.5
(Uizuno 1
0
0
1
2
3
4
5
VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics

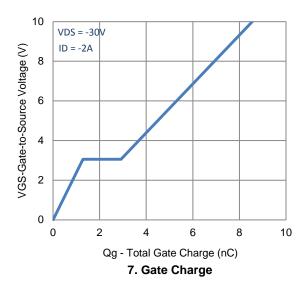


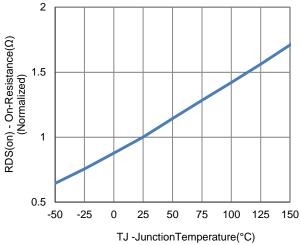
4. Drain-to-Source Forward Voltage

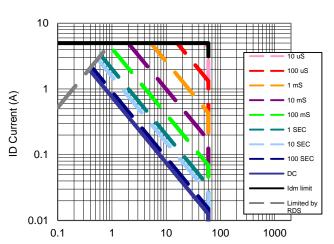


6. Capacitance

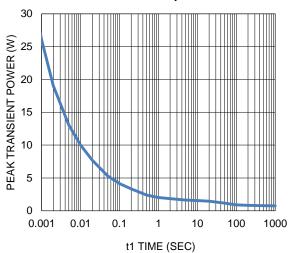
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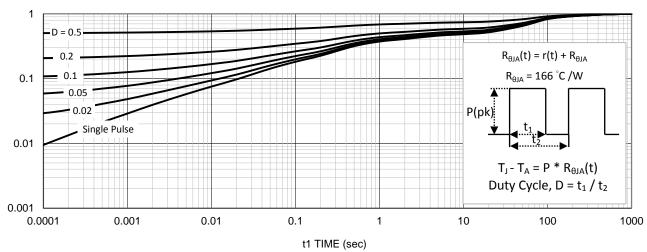
8. Normalized On-Resistance Vs Junction Temperature



VDS Drain to Source Voltage (V)

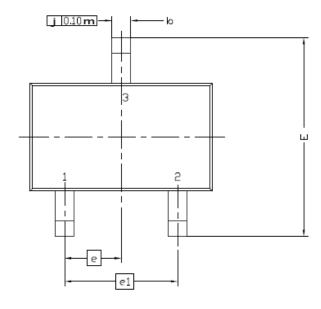
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

# Package Information



DIM.	MILLIMETERS			INCHES				
	MIN	NDM	MAX	MIN	NDM	MAX		
Α	0.900	0,95	1.10	0,035	0,037	0.043		
A1	0.00		0.10	0.000		0.004		
A2	0.70	0.90	1.00	0.028	0.035	0.039		
lo	0.15	0.22	0.30	0.006	0.016	0.012		
C	0.08	0.127	0.20	0.003	0.005	0.008		
D	ć	2.10 BS	C	0.	083 B2	B3 B2C		
E	2.30 BSC			0.091 BSC				
E1	1,30 BSC			0.051 BSC				
6	0.65 BSC			0.026 BSC				
€1	1.30 BSC			0.051 BSC				
L	0.26	0.40	0.46	0,010	0,015	0.018		
L2	0.254BSC			0.010BSC				
R	0.10			0.004				
θ	0°	4°	8°	0°	4°	8°		
θ1		7°NDM 7°NDM				·		

